

DESCRIPTION

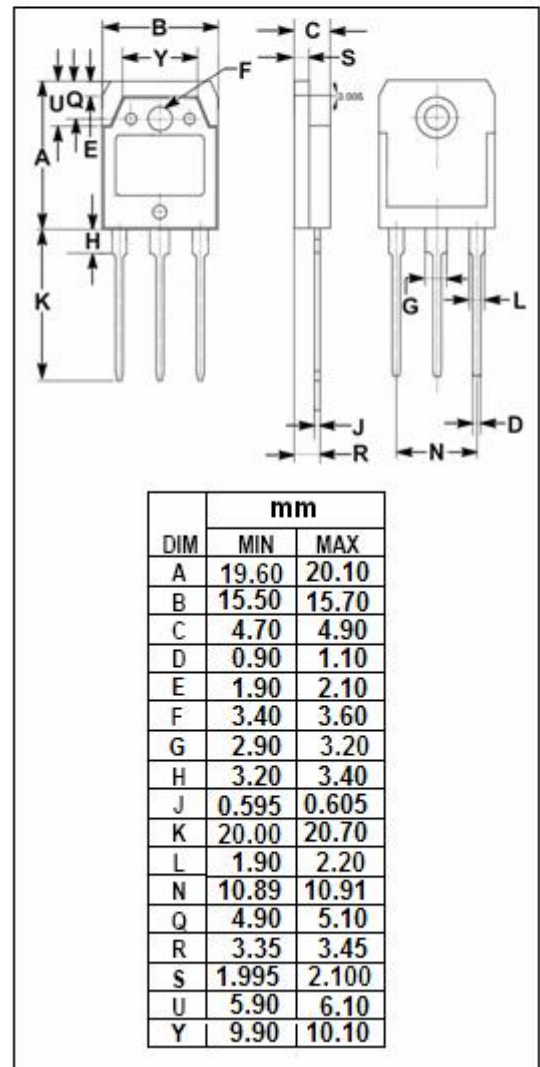
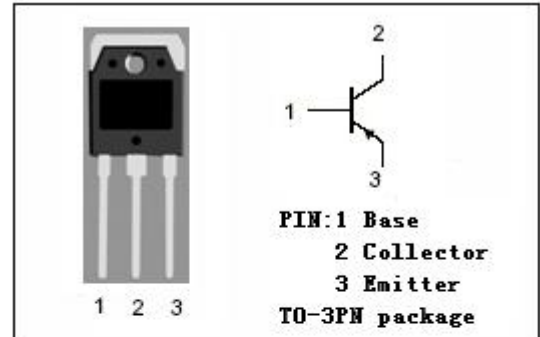
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min})$
- High Current Capability
- Wide Area of Safe Operation
- Complement to Type 2SD1840

APPLICATIONS

- Designed for motor drivers, converters and other general High-current switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-110	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-15	A
I_{CP}	Collector Current-Pulse	-25	A
I_B	Base Current-Continuous	-5	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	3	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	100	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



SPTECH Silicon PNP Power Transistor**2SB1230****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -5mA ; R _{BE} =∞	-100			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA; I _E = 0	-110			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -6A; I _B = -0.6A			-0.8	V
V _{BE(sat)}	Base -Emitter Saturation Voltage	I _C = -6A; I _B = -0.6A			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -100V; I _E = 0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-100	μ A
h _{FE-1}	DC Current Gain	I _C = -1.5A; V _{CE} = -2V	50		140	
h _{FE-2}	DC Current Gain	I _C = -6A; V _{CE} = -2V	20			

◆ **h_{FE-1} Classifications**

P	Q
50-100	70-140